

ALTERNATIVE TO PTO/SB/08A/B  
(Based on PTO 03-08 version)

Substitute for form 1449/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)		Application Number	10/537,804
		Filing Date	June 7, 2005
		First Named Inventor	Robert DWILINSKI
		Art Unit	1792
		Examiner Name	F.C. Hiteshew
Sheet	1	of	5
		Attorney Docket Number	204552035400

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<b>Sheet</b>	2	of	5
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Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T <sup>2</sup>
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Examiner Signature	/Felisa Hiteshew/	Date Considered	10/07/2008
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